

LIST OF CURRENT CLAIMS

1(Currently Amended). A method for producing vertically integratable circuits, comprising producing electrically conductive contacts for vertical integration ~~by simultaneously while~~ producing the integratable circuits themselves, electrically conductive contacts for vertical integration and electrically conductive contacts of the integrated circuit in a continuous process.

B6 2(Currently Amended). The method according to claim 1, comprising the steps:

a) producing an insulation at the places of the contacts for vertical integration ~~from a front side of~~ on a front side in a thickness direction of a substrate bearing the vertically integratable circuits,

b) producing a gap within the insulations from the front side,

c) filling the gaps with an electroconductive material from the front side to form at least some of the contacts,

d) exposing the electroconductive material from a ~~backside~~ rear side opposite the front side of the substrate bearing the vertically integratable circuits at the places of the contacts for vertical integration, and

e) applying an electroconductive material from the ~~backside~~ rear side to the previously exposed electric material at the places of the contacts for vertical integration to form at least some of the contacts.

3(Currently Amended). The method according to claim 2, including thinning the substrate from the ~~backside~~ rear side before exposure of the electroconductive material from the ~~backside~~ rear side.

4(Previously Presented). The method according to claim 3, wherein the substrate has a hidden insulating layer and thinning is performed up to said insulating layer.

5(Previously Presented). The method according to claim 3, wherein thinning is performed until the insulation produced for the contacts for vertical integration is reached.

6(Previously Presented). The method according to claim 2, wherein the insulation produced in method step a) is produced during production of field oxide, including forming gaps in the substrate that enclose substrate material that oxidizes completely during production of the field oxide.

7(Previously Presented). The method according to claim 2, wherein the gaps produced in method step b) within the insulations and the filling of said gaps according to method step c) with an electroconductive material are performed during production of a metalization level with associated through holes.

8(Previously Presented). The method according to claim 2, including applying the electroconductive material applied in method step e) in a backside metalization.

9(Currently Amended). A vertically integratable circuit having electrically conductive contacts for electrically conductive connection with further vertically integratable circuits, comprising electrically conductive contacts ~~used for~~ arranged for vertical integration and associated insulations produced simultaneously during production of the forming part of the vertically integratable circuit itself, said electrically conductive contacts having exposed end portions disposed along opposed front and rear sides in a thickness direction of the vertically integratable circuit.

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10(Previously Presented). The vertically integratable circuit according to claim 9, wherein at least two vertically integratable circuits are connected, and include electrically conductive contacts for vertical integration that are electrically connected with each other.
